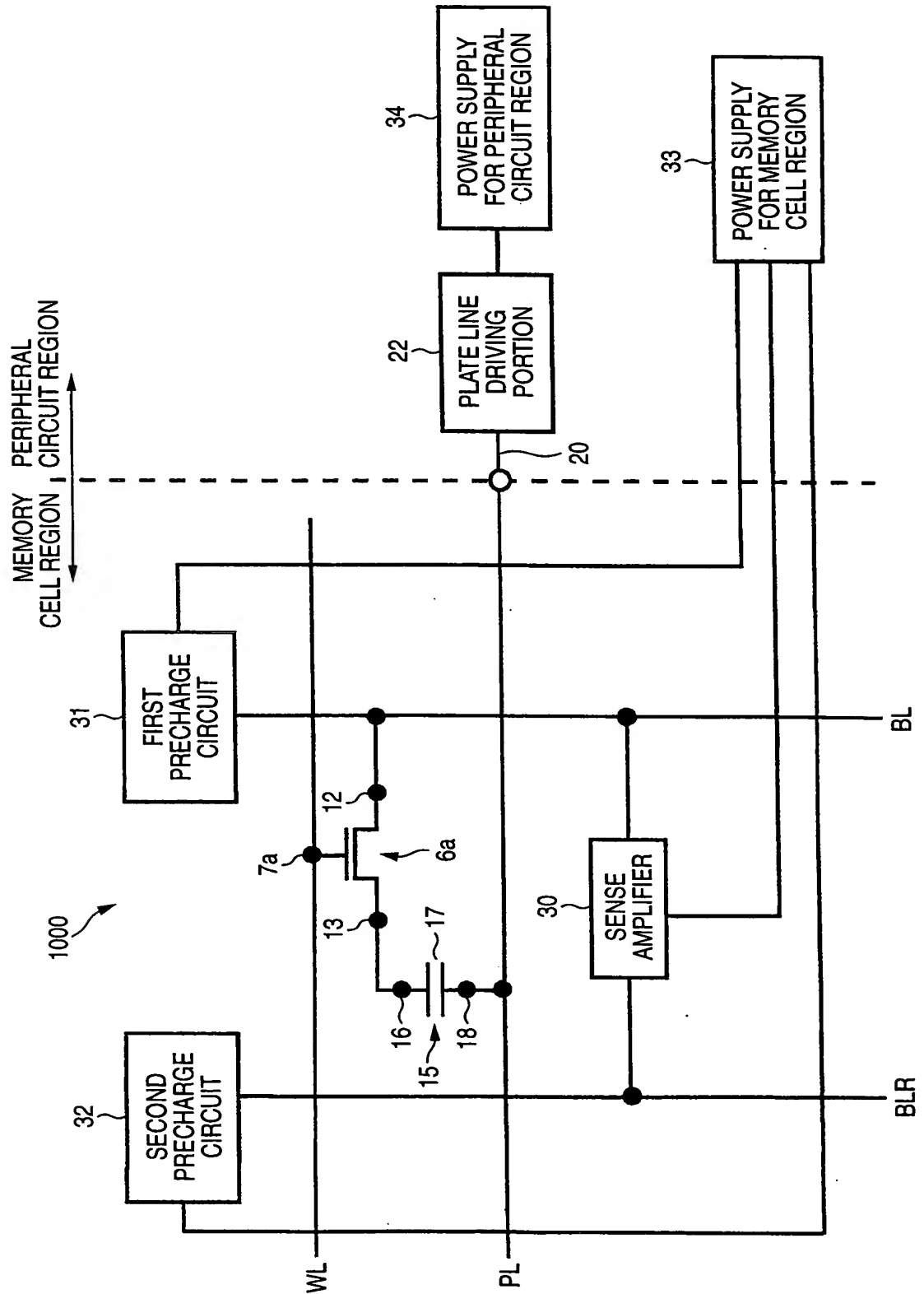


FIG. 1



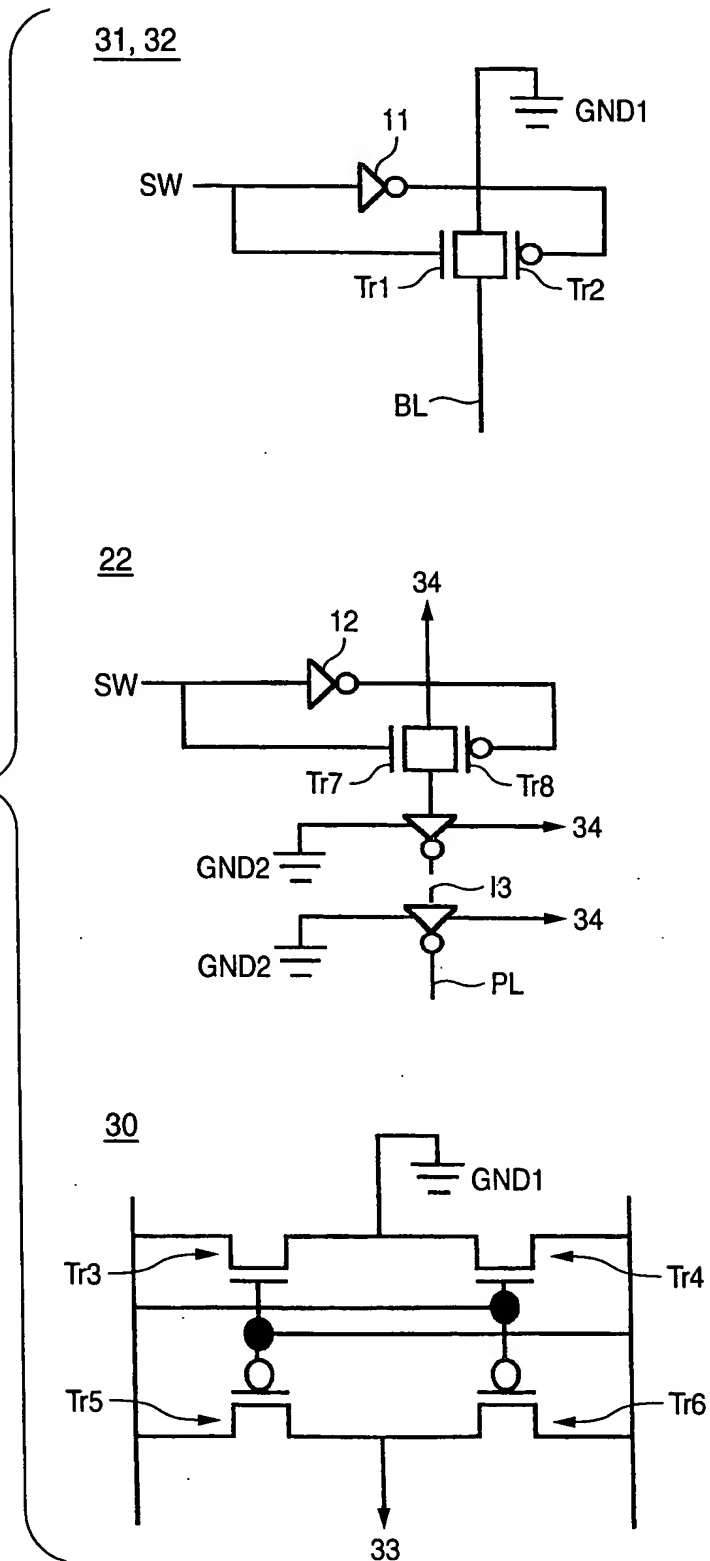


FIG. 3A

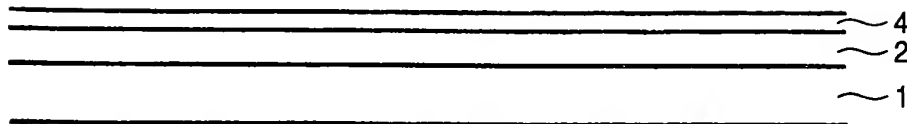


FIG. 3B

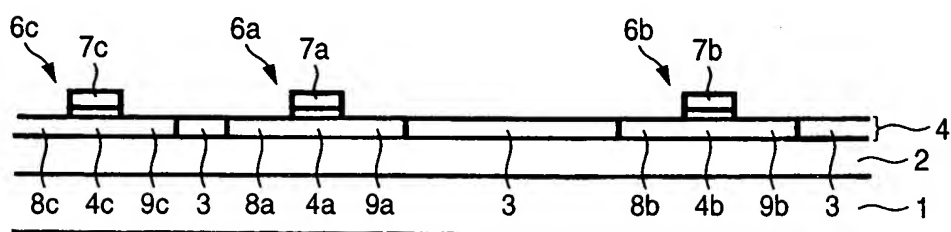


FIG. 3C

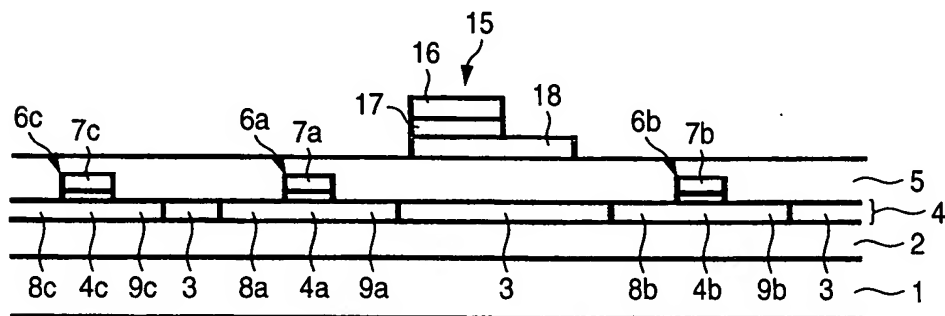
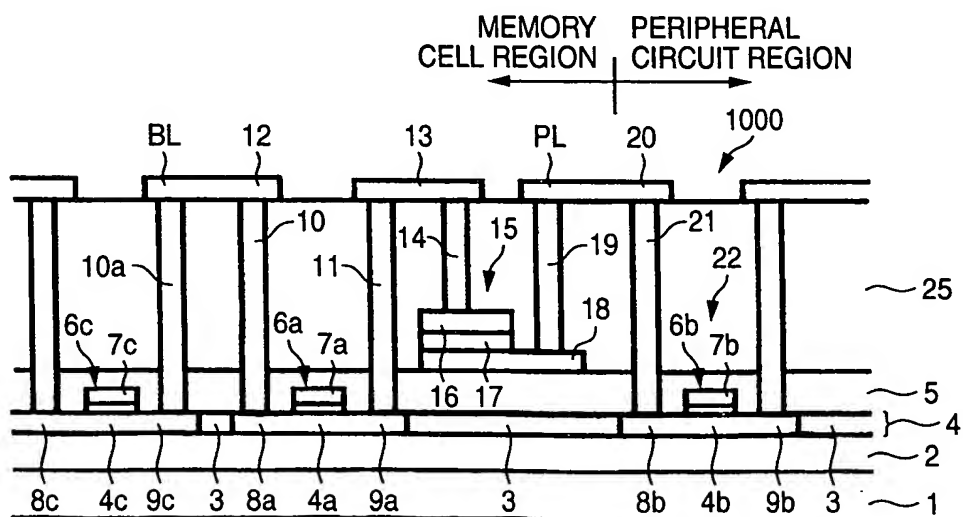
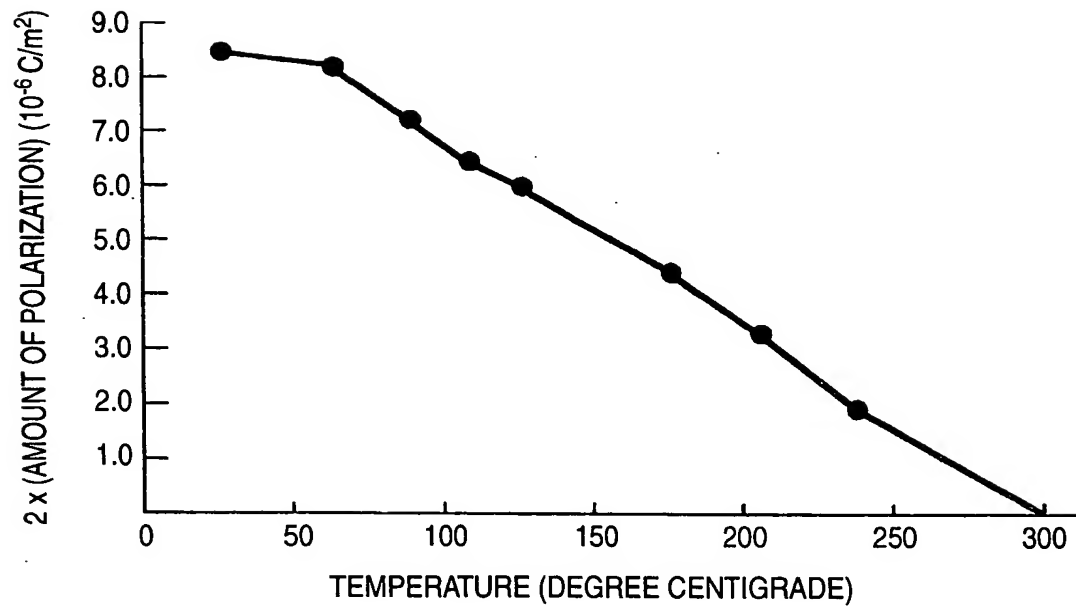


FIG. 3D



4/13

*FIG. 4*



5/13

FIG. 5

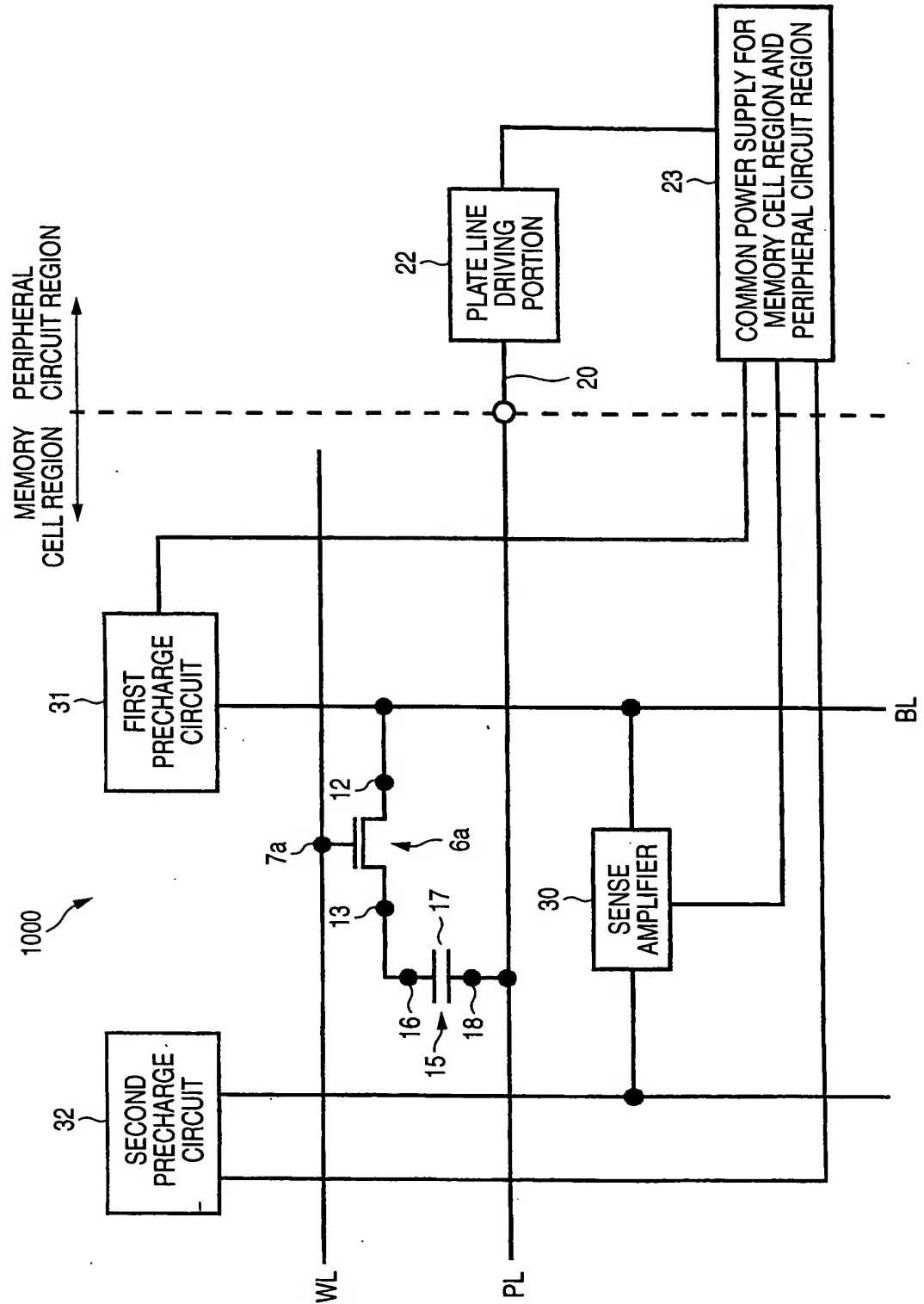


FIG. 6

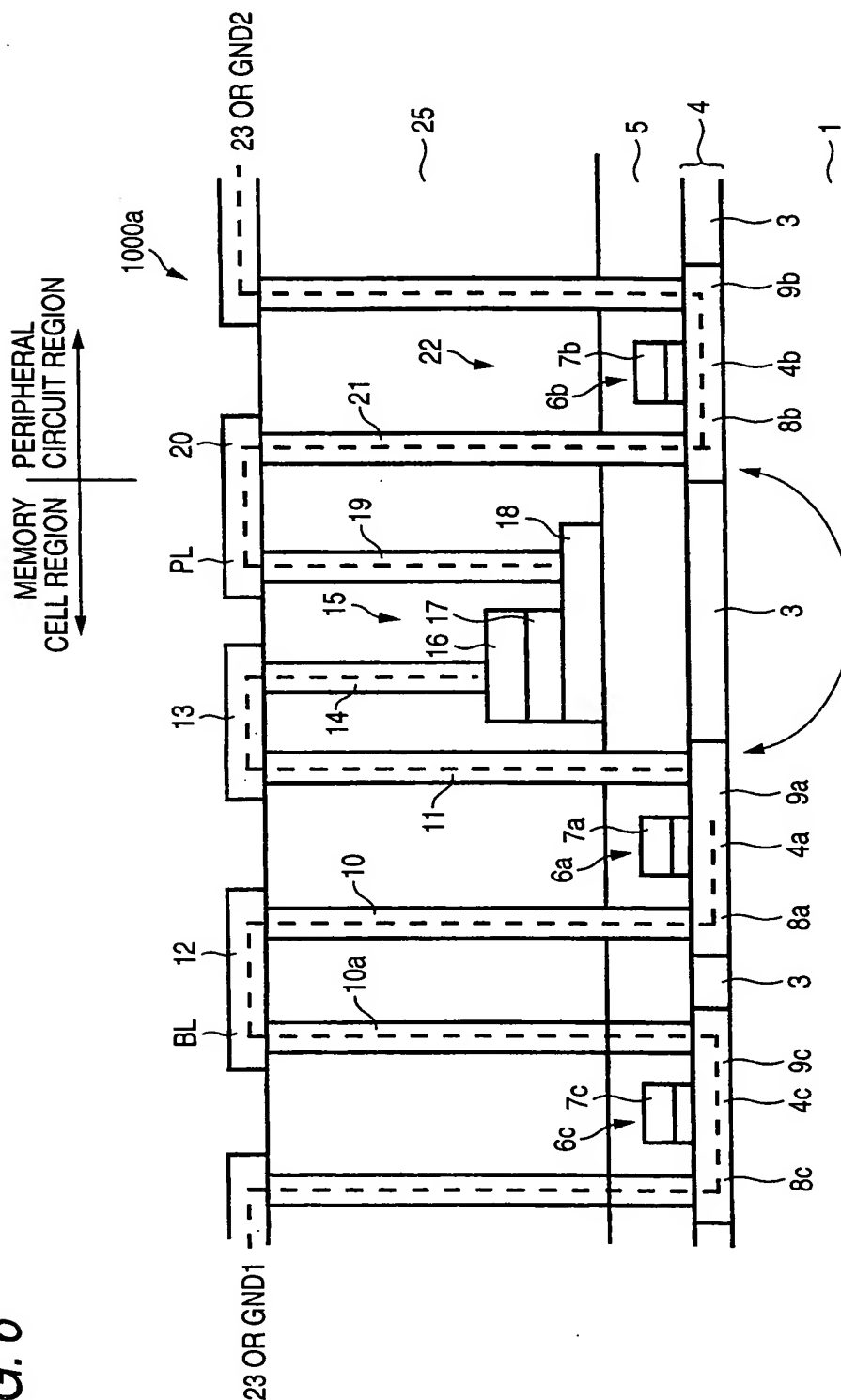


FIG. 7A

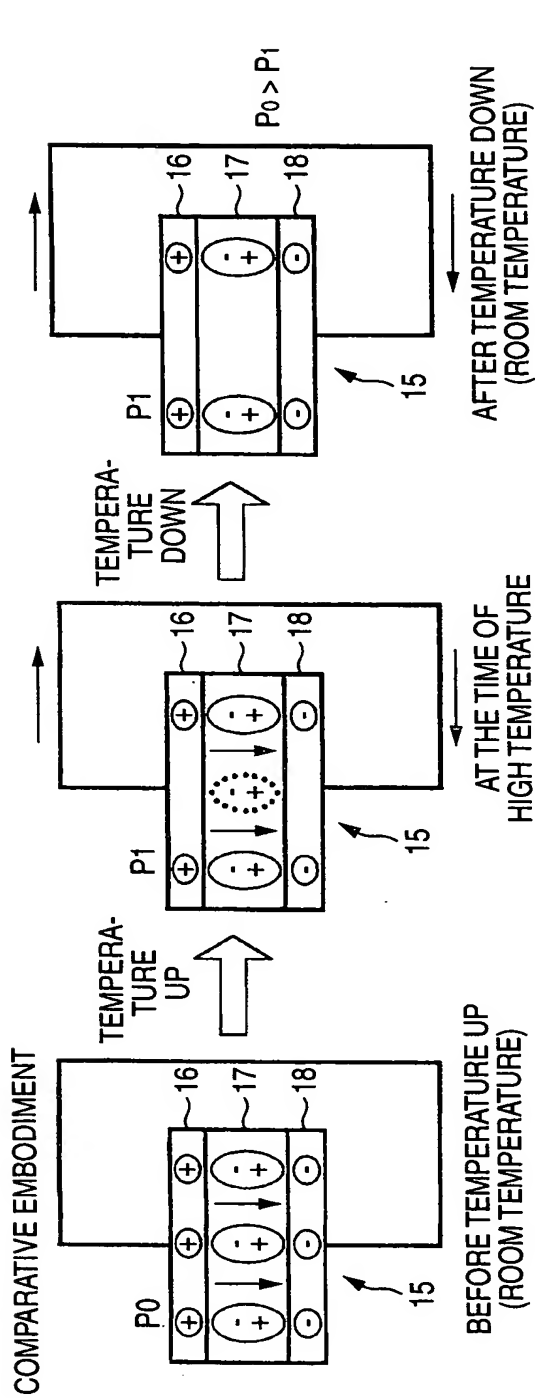
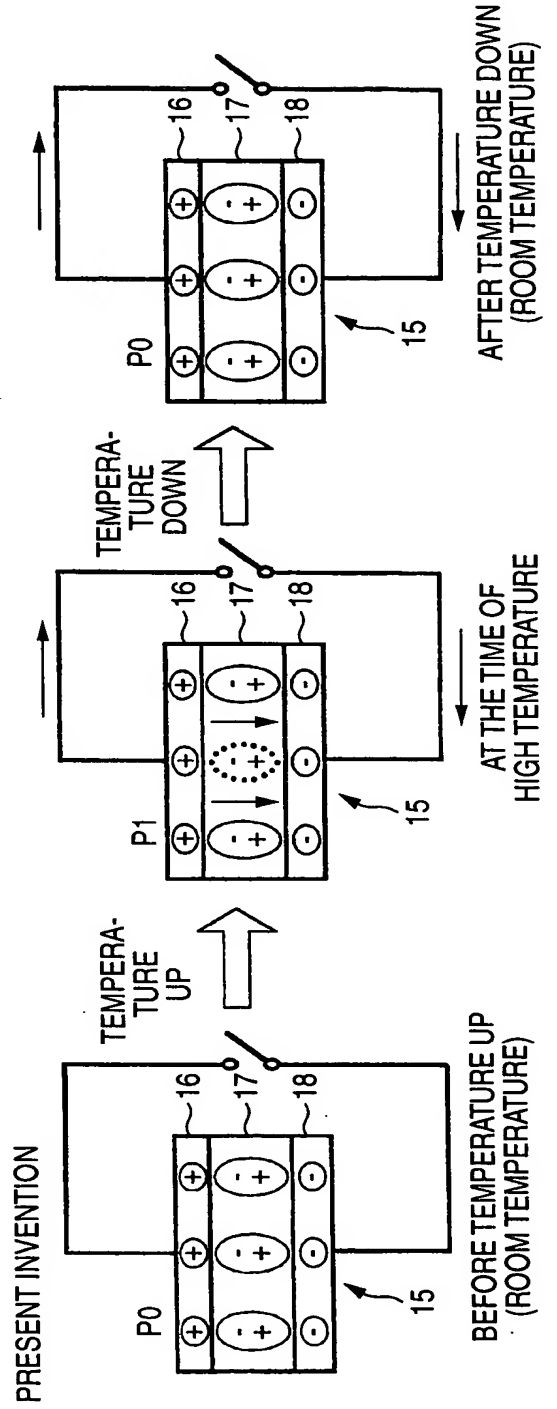
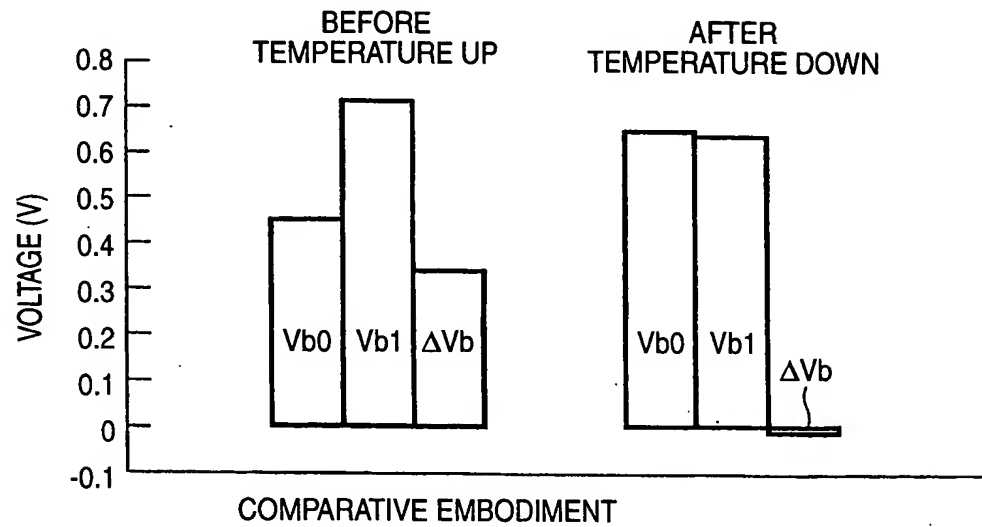


FIG. 7B

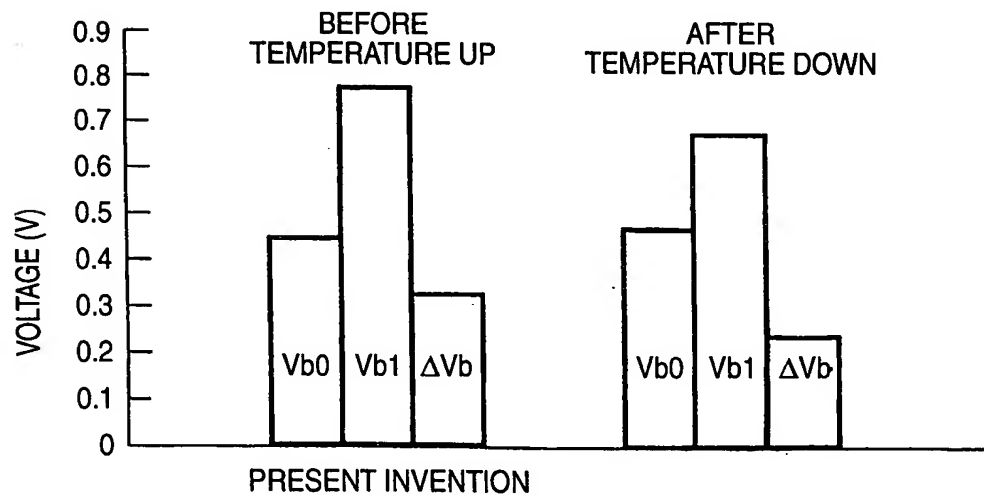


8/13

**FIG. 8A**



**FIG. 8B**





9/13

FIG. 9A

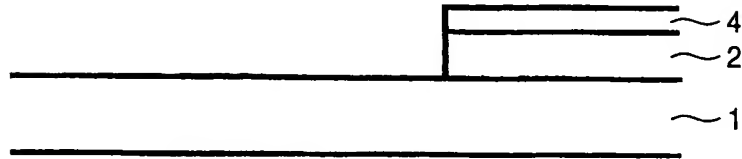


FIG. 9B

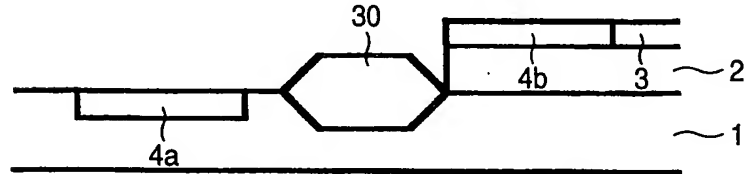


FIG. 9C

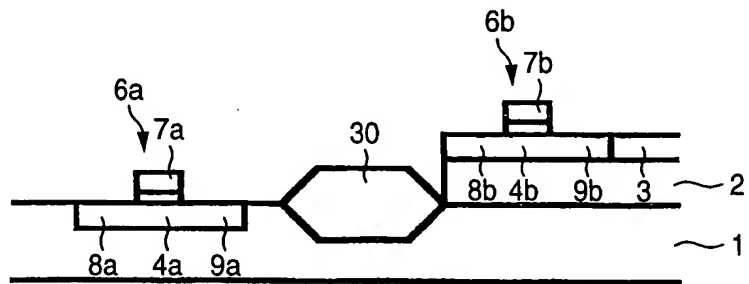


FIG. 9D

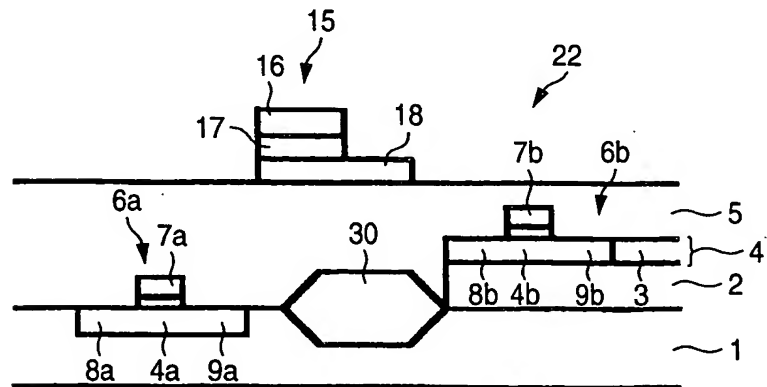


FIG. 10

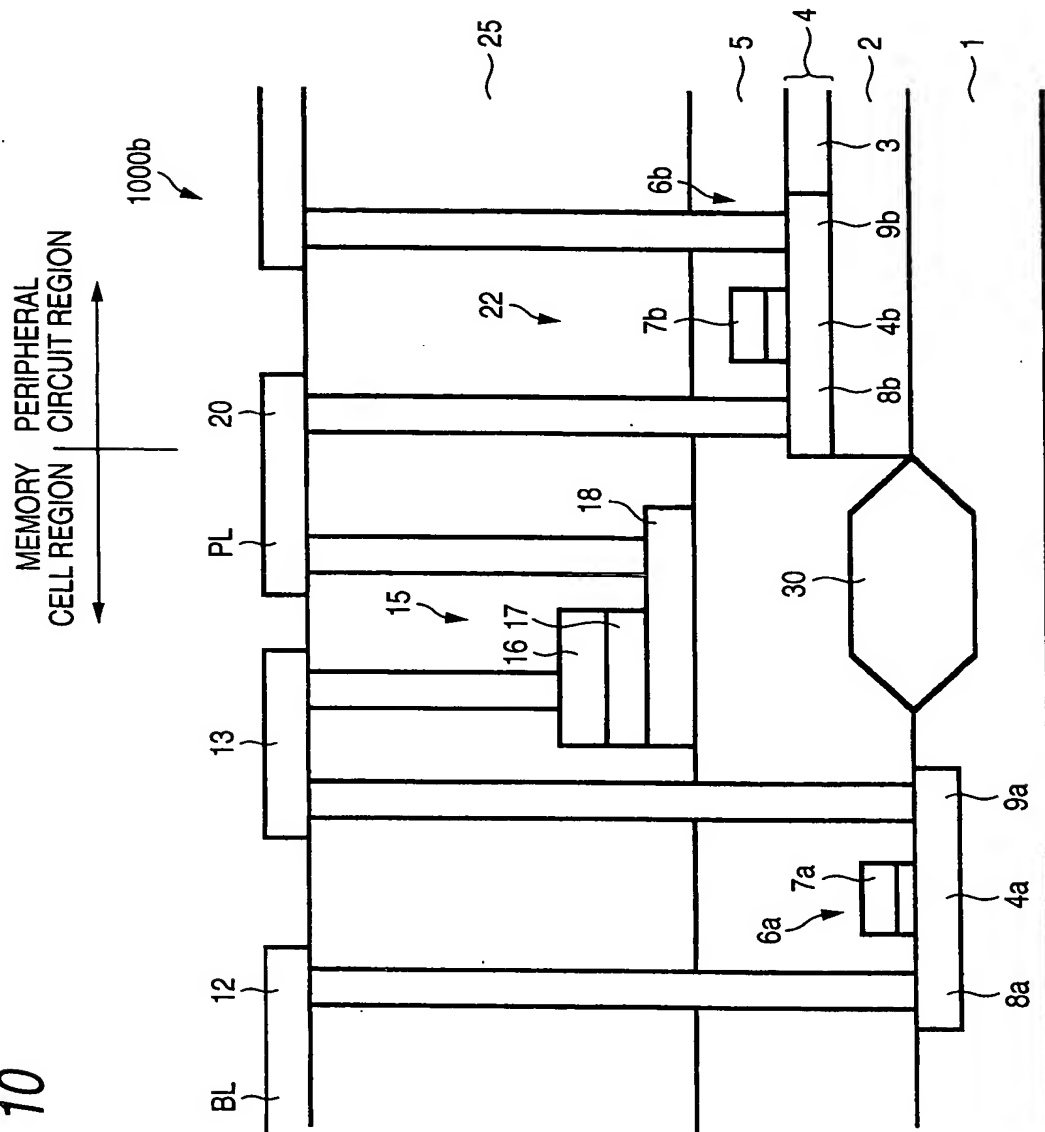


FIG. 11A

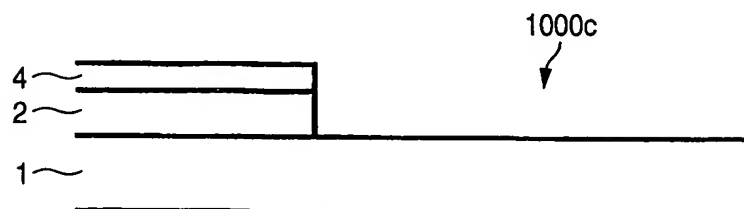


FIG. 11B

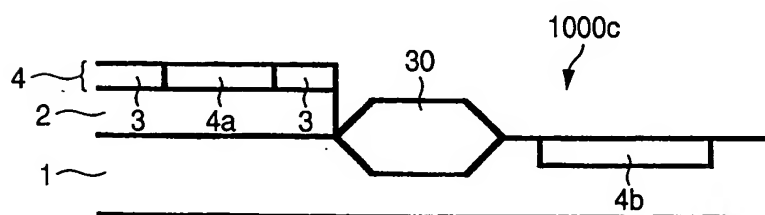


FIG. 11C

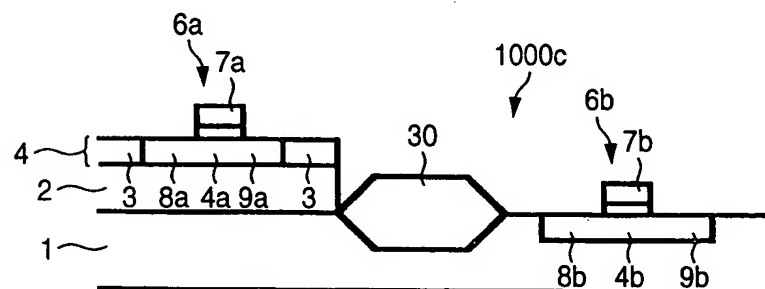


FIG. 11D

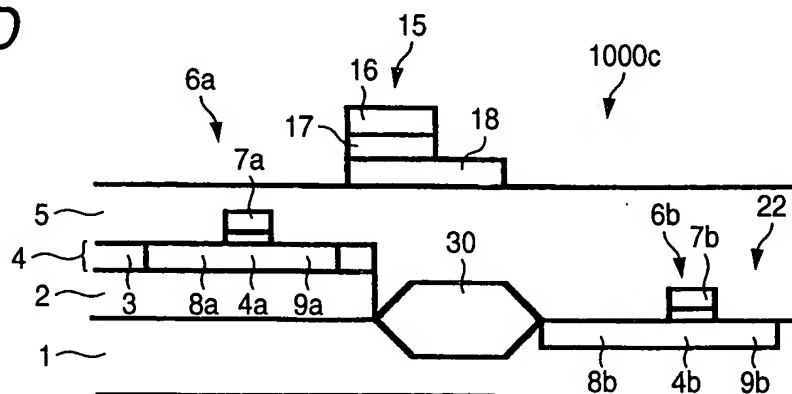


FIG. 12

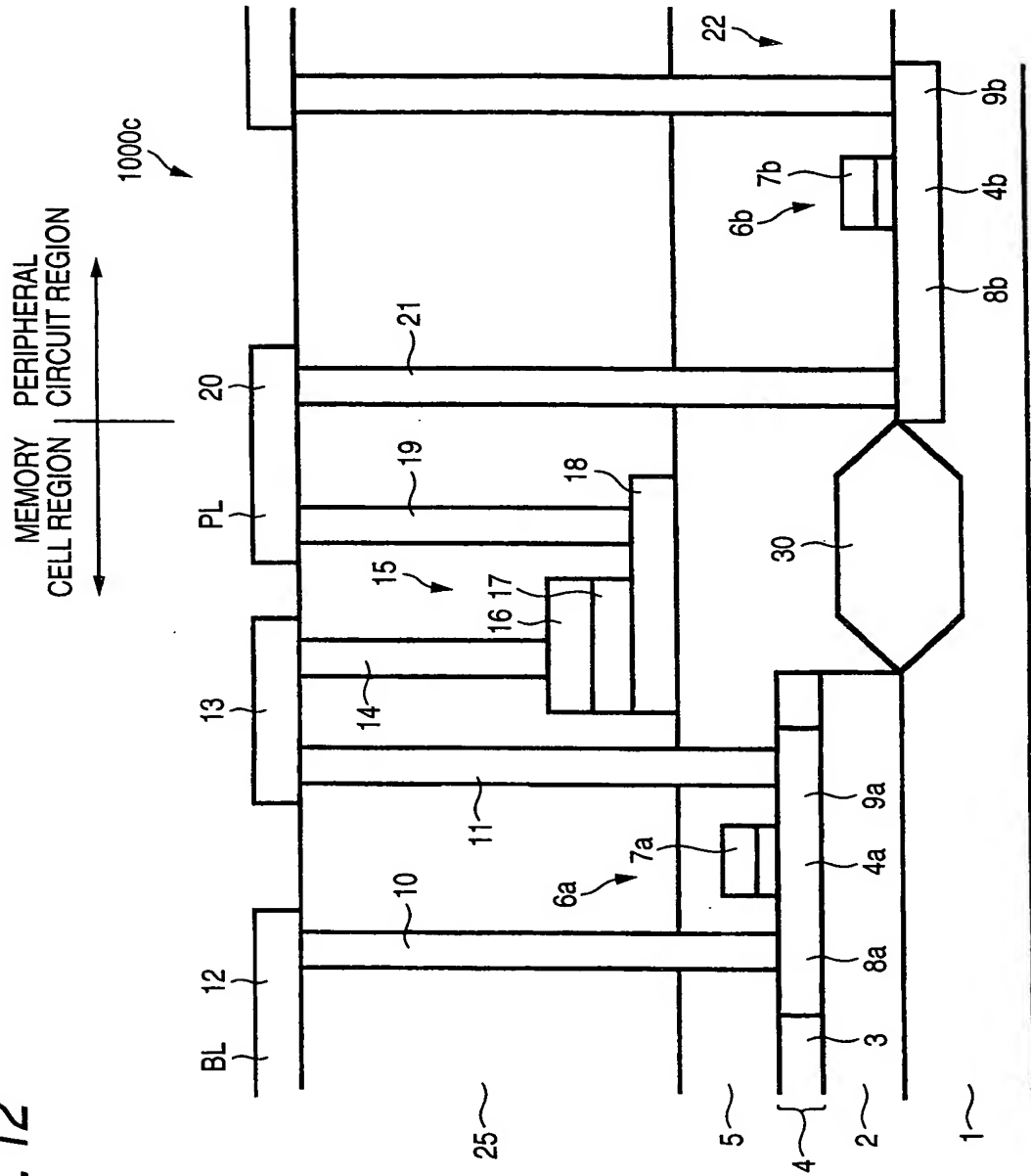


Fig. 13A is a plan view of a semiconductor device. It shows a substrate 1a with a gate 4a in the MEMORY CELL REGION and a gate 4b in the PERIPHERAL CIRCUIT REGION. A dimension 1000d is indicated for the peripheral circuit region.

**Fig. 13B**

This diagram shows a cross-sectional view of another embodiment of the semiconductor device. It features a substrate 1a and a base layer 5. A gate stack 6a is formed over the substrate, with a gate electrode 7a. A source/drain region 8a is located under the gate stack, and a contact pad 9a is formed over it. A memory cell region is defined by a vertical wall 15, a word line 16, and a bit line 18. The peripheral circuit region includes a gate stack 6b, a gate electrode 7b, a source/drain region 8b, and a contact pad 9b. A label 1000d points to the peripheral circuit region.